

isc

N-Channel

MOSFET

Transistor

IRF730FI

DESCRIPTION

- Drain Current $-I_D=3.5A@ T_C=25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS}= 400V(Min)$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 1.0 \Omega (Max)$
- Fast Switching Speed

APPLICATIONS

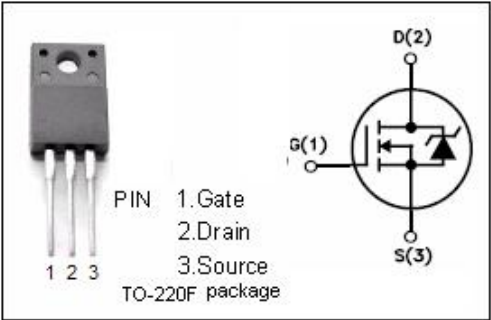
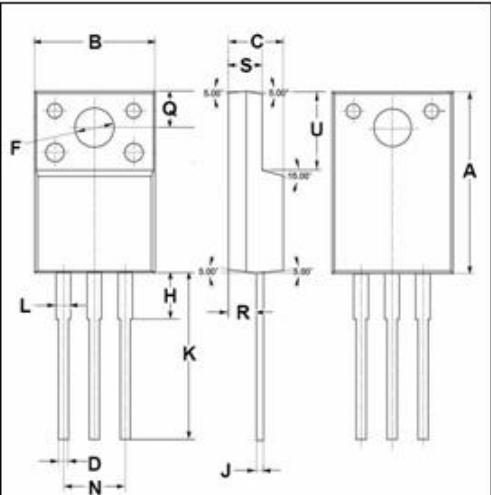
- Designed especially for high voltage,high speed applications, such as off-line switching power supplies , UPS,AC and DC motor controls,relay and solenoid drivers.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	400	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=25^{\circ}C$	3.5	A
P_{tot}	Total Dissipation@ $TC=25^{\circ}C$	35	W
T_j	Max. Operating Junction Temperature	-55~150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.67	$^{\circ}C/W$
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	80	$^{\circ}C/W$



DIM	mm	
	MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.80
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

isc N-Channel Mosfet Transistor**IRF730FI****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 0.25mA	400		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 0.25mA	2	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 3.0A		1.0	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0		±500	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 400V; V _{GS} = 0		250	uA
V _{SD}	Diode Forward Voltage	I _F = 3.5A; V _{GS} = 0		1.6	V